

Silicon NPN transistor in a TO-92 Plastic Package.

High voltage, low saturation, low C_{cb} .

High voltage control circuit.

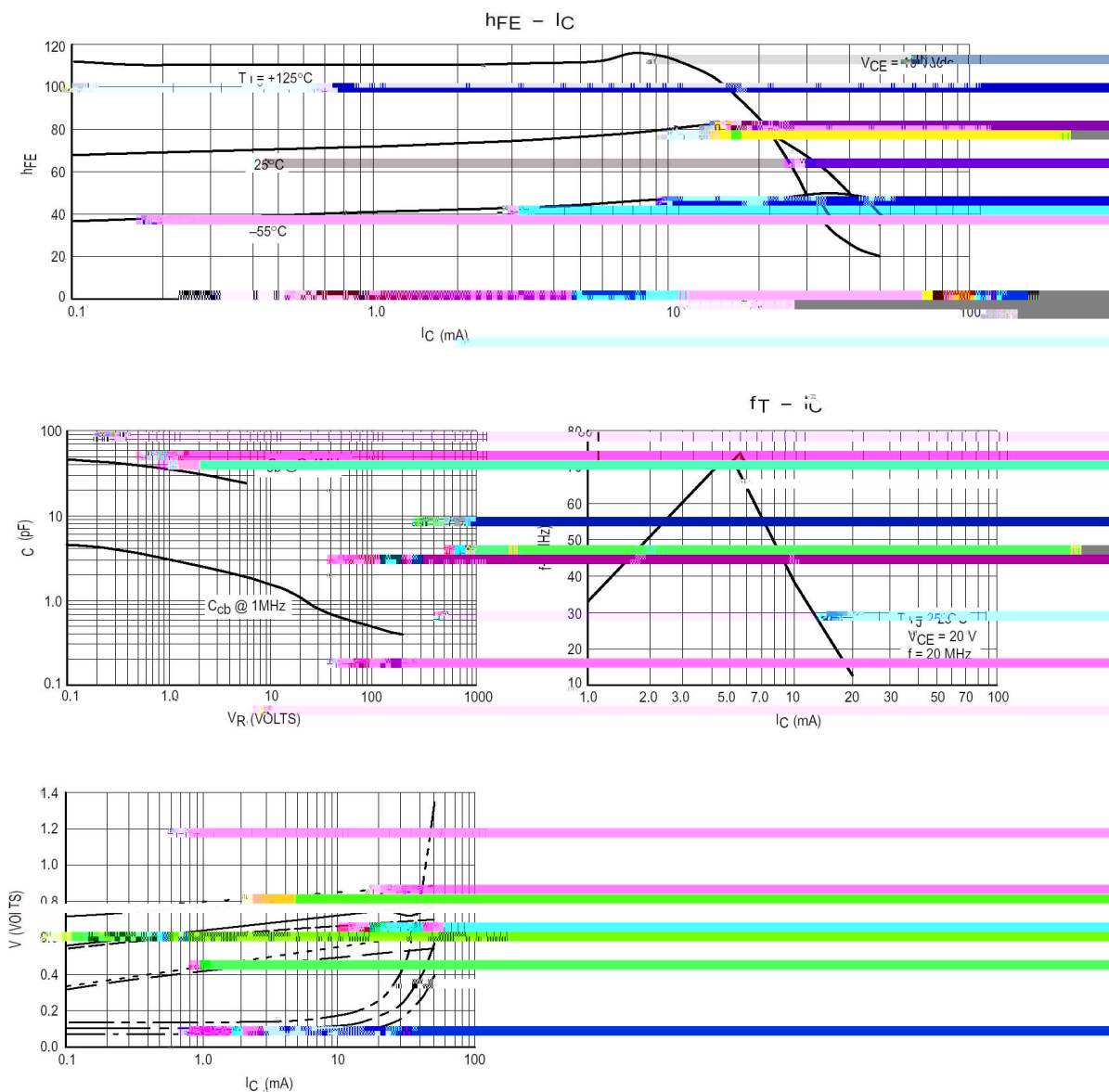
/ Absolute Maximum Ratings(Ta=25)

Parameter	Symbol	Rating	Unit
Collector to Base Voltage	V_{CBO}	200	V
Collector to Emitter Voltage	V_{CEO}	200	V
Emitter to Base Voltage	V_{EBO}	6.0	V
Collector Current - Continuous	I_C	500	mA
Collector Power Dissipation	P_C	625	mW
Junction Temperature	T_j	150	
Storage Temperature Range	T_{stg}	-55 150	

/ Electrical Characteristics(Ta=25)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector to Base Breakdown Voltage	V_{CBO}	$I_C=100\mu A$ $I_E=0$	200			V
Collector to Emitter Breakdown Voltage	V_{CEO}	$I_C=1.0mA$ $I_B=0$	200			V
Emitter to Base Breakdown Voltage	V_{EBO}	$I_E=100\mu A$ $I_C=0$	6.0			V
Collector Cut-Off Current	I_{CBO}	$V_{CB}=160V$ $I_E=0$			0.1	μA
Emitter Cut-Off Current	I_{EBO}	$V_{EB}=4.0V$ $I_C=0$			0.1	μA
DC Current Gain	$h_{FE(1)}$	$V_{CE}=10V$ $I_C=10mA$	40			
	$h_{FE(2)}$	$V_{CE}=10V$ $I_C=30mA$	40			
	$h_{FE(3)}$	$V_{CE}=10V$ $I_C=1.0mA$	25			
Collector to Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C=20mA$ $I_B=2.0mA$			0.5	V
Base to Emitter Saturation Voltage	$V_{BE(sat)}$	$I_C=20mA$ $I_B=2.0mA$			0.9	V
Transition Frequency	f_T	$V_{CE}=20V$ $f=100MHz$ $I_C=10mA$	50			MHz
Output Capacitance	C_{ob}	$V_{CB}=20V$ $f=1.0MHz$ $I_E=0$			4.0	pF

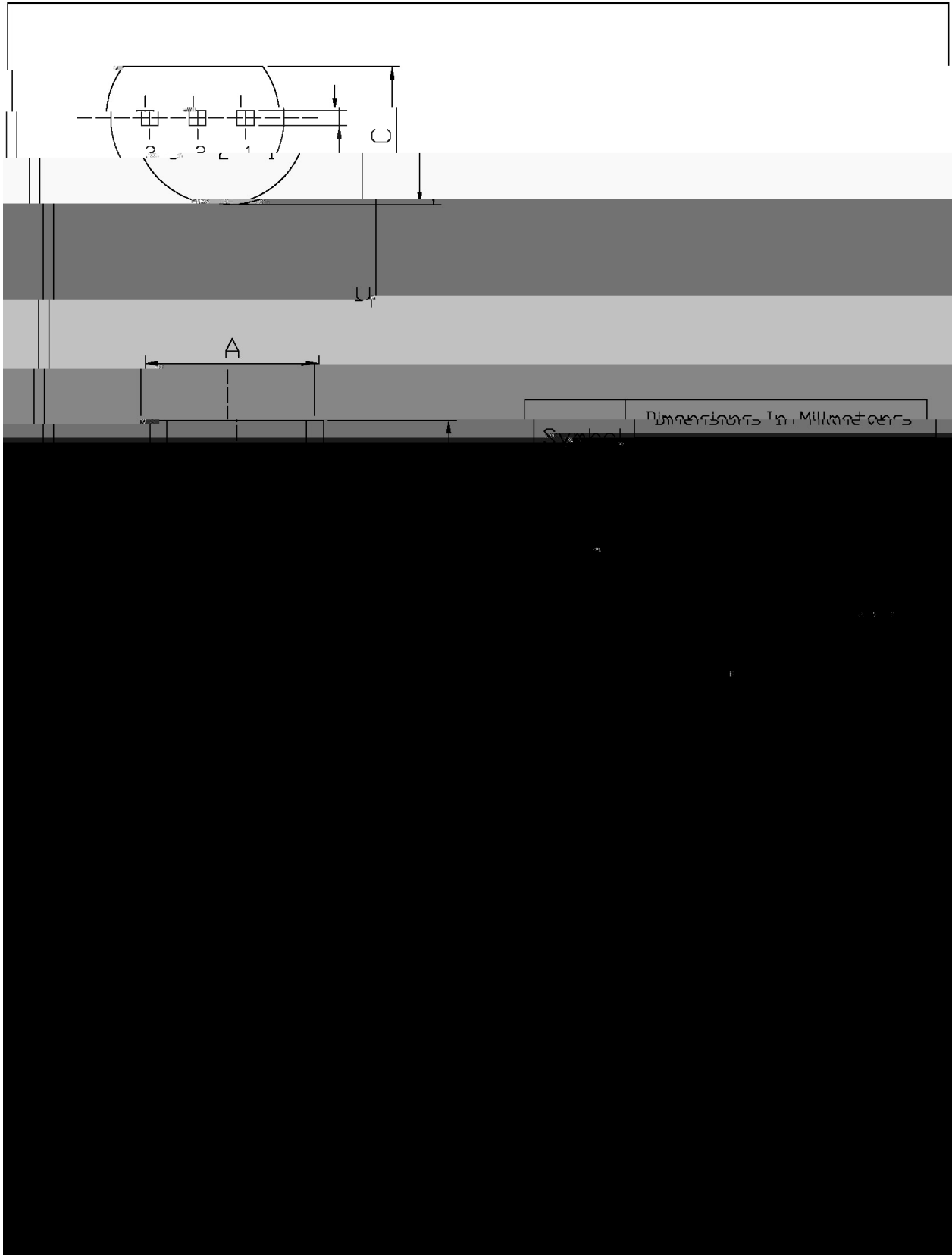
/ Electrical Characteristic Curve



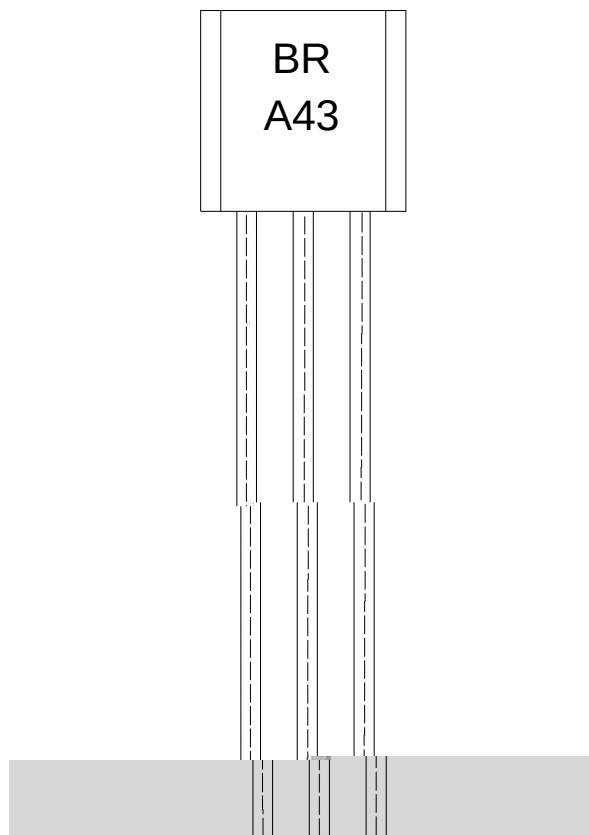
/ Package Dimensions

TO-92

Unit: mm



/ Marking Instructions



Note:

BR: Company Code.

A43: Product Type.

***: Lot No. Code,code change with Lot No.

